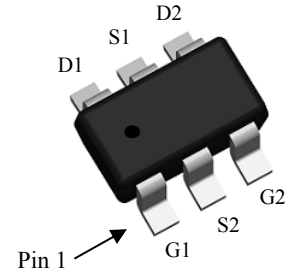


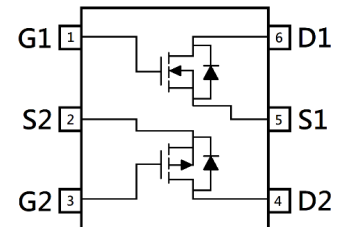
	N-CH	P-CH
BV_{DSS}	30V	-30V
$I_D @ V_{GS}=(-)10V, T_A=25^{\circ}C$	4.6A	-3.5A
$R_{DS(ON) typ. @ V_{GS}=(-)10V}$	19 m Ω	41m Ω
$R_{DS(ON) typ. @ V_{GS}=(-)4.5V}$	25m Ω	57m Ω



TSOP-6

Features

- Low On Resistance
- Low Gate Charge
- Fast Switching Characteristic



G : Gate S : Source D : Drain

Absolute Maximum Ratings ($T_A=25^{\circ}C$)

Parameter	Symbol	Limits		Unit
		N-CH	P-CH	
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 20	± 20	
Continuous Drain Current @ $V_{GS}=(-)10V, T_A=25^{\circ}C$	I_D	4.6	-3.5	A
Continuous Drain Current @ $V_{GS}=(-)10V, T_A=70^{\circ}C$		3.7	-2.8	
Pulsed Drain Current	I_{DM}	18	14	
Continuous Body Diode Forward Current @ $T_A=25^{\circ}C$	I_S	0.9	-0.9	
Avalanche Current @ $L=0.1mH$	I_{AS}	10	-9	mJ
Avalanche Energy @ $L=0.5mH$	E_{AS}	9	6.3	
Total Power Dissipation	$T_A=25^{\circ}C$	1.1		W
	$T_A=70^{\circ}C$			
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150		$^{\circ}C$

Thermal Data

Parameter	Symbol	Steady State	Unit
Thermal Resistance, Junction-to-ambient	$R_{\theta JA}$	113	$^{\circ}C/W$

N-Channel Electrical Characteristics (T_A=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	30	-	-	V	V _{GS} =0V, I _D =250μA
V _{GS(th)}	1	-	2.5		V _{DS} =V _{GS} , I _D =250μA
G _{FS}	-	5.4	-	S	V _{DS} =10V, I _D =3A
I _{GSS}	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V
I _{DSS}	-	-	1	μA	V _{DS} =24V, V _{GS} =0V
R _{DS(ON)}	-	19	25	mΩ	V _{GS} =10V, I _D =4A
	-	25	35		V _{GS} =4.5V, I _D =3A
Dynamic					
C _{iss}	-	510	-	pF	V _{DS} =15V, V _{GS} =0V, f=1MHz
C _{oss}	-	75	-		
C _{rss}	-	58	-		
R _g	-	4.5	-	Ω	f=1MHz
Q _g *1, 2	-	13	-	nC	V _{DS} =15V, I _D =6A, V _{GS} =10V
Q _{gs} *1, 2	-	1.6	-		
Q _{gd} *1, 2	-	2.5	-		
t _{d(ON)} *1, 2	-	5.6	-	ns	V _{DS} =15V, I _D =6A, V _{GS} =10V, R _{GS} =1Ω
t _r *1, 2	-	7.5	-		
t _{d(OFF)} *1, 2	-	26	-		
t _f *1, 2	-	4.5	-		
Source-Drain Diode					
V _{SD} *1	-	0.85	1.2	V	I _S =6A, V _{GS} =0V
t _{rr}	-	7	-	ns	I _F =6A, dI _F /dt=100A/μs
Q _{rr}	-	3	-	nC	

Note:

*1. Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

*2. Independent of operating temperature

P-Channel Electrical Characteristics (T_A=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	-30	-	-	V	V _{GS} =0V, I _D =-250μA
V _{GS(th)}	-1	-	-2.5		V _{DS} =V _{GS} , I _D =-250μA
G _{FS}	-	5.4	-	S	V _{DS} =-10V, I _D =-5A
I _{GSS}	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V
I _{DSS}	-	-	-1	μA	V _{DS} =-24V, V _{GS} =0V
R _{DS(ON)}	-	41	54	mΩ	V _{GS} =-10V, I _D =-3A
	-	57	80		V _{GS} =-4.5V, I _D =-2A
Dynamic					
C _{iss}	-	640	-	pF	V _{DS} =-15V, V _{GS} =0V, f=1MHz
C _{oss}	-	75	-		
C _{rss}	-	65	-		
R _g	-	25	-	Ω	f=1MHz
Q _g *1, 2	-	14	-	nC	V _{DS} =-15V, I _D =-5A, V _{GS} =-10V
Q _{gs} *1, 2	-	2	-		
Q _{gd} *1, 2	-	3	-		
t _{d(ON)} *1, 2	-	6	-	ns	V _{DS} =-15V, I _D =-5A, V _{GS} =-10V, R _{GS} =1Ω
t _r *1, 2	-	18	-		
t _{d(OFF)} *1, 2	-	50	-		
t _f *1, 2	-	16	-		
Source-Drain Diode					
V _{SD} *1	-	-0.8	-1.2	V	I _S =-1.7A, V _{GS} =0V
t _{rr}	-	7.7	-	ns	I _F =-1.7A, dI _F /dt=100A/μs
Q _{rr}	-	2.9	-	nC	

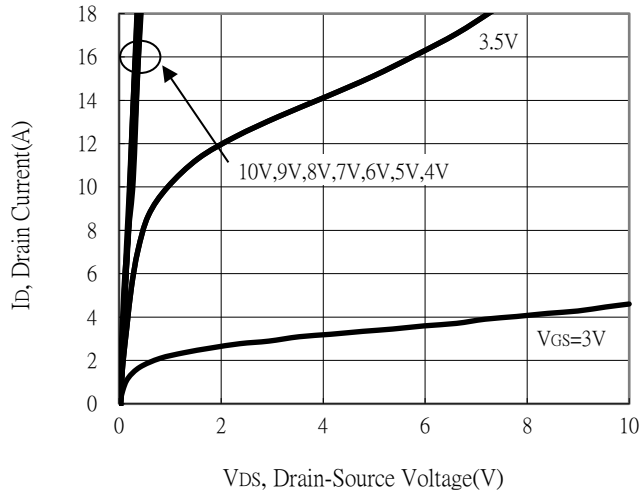
Note:

*1. Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

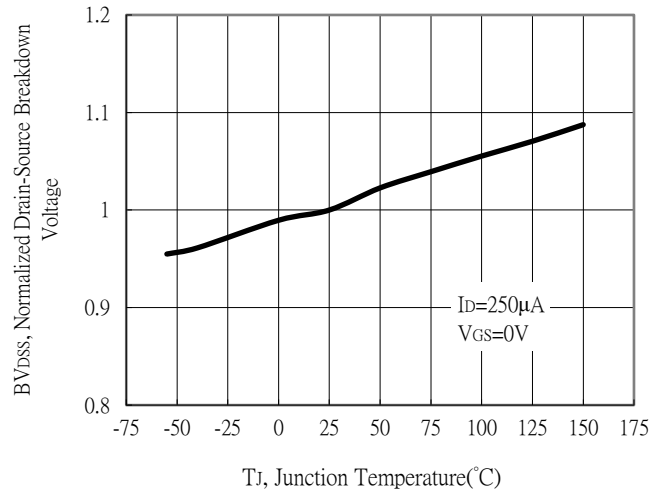
*2. Independent of operating temperature

Typical Characteristics : Q1(N-channel)

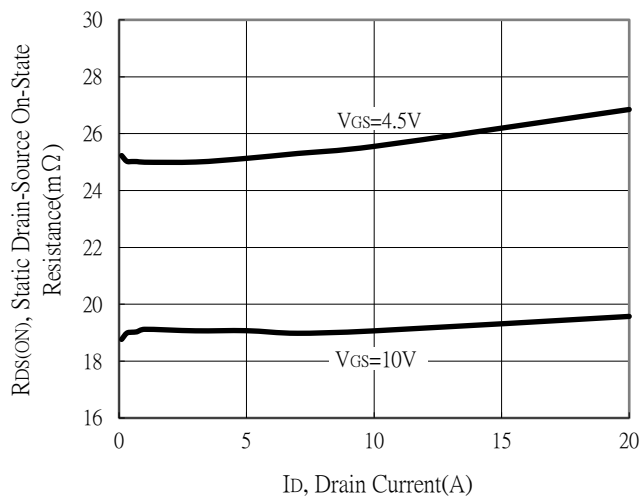
Typical Output Characteristics



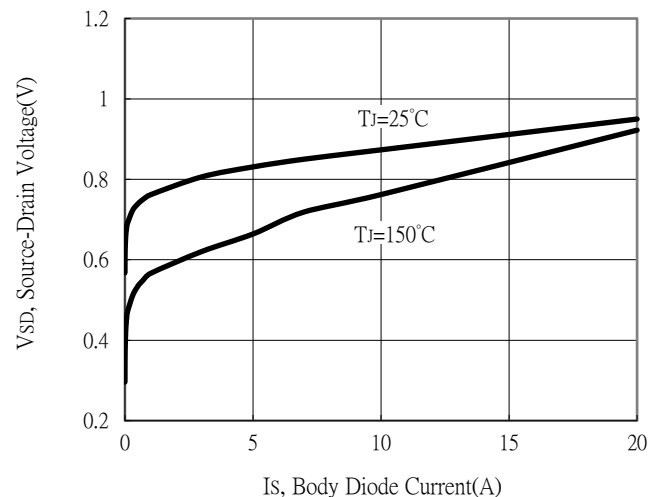
Breakdown Voltage vs Ambient Temperature



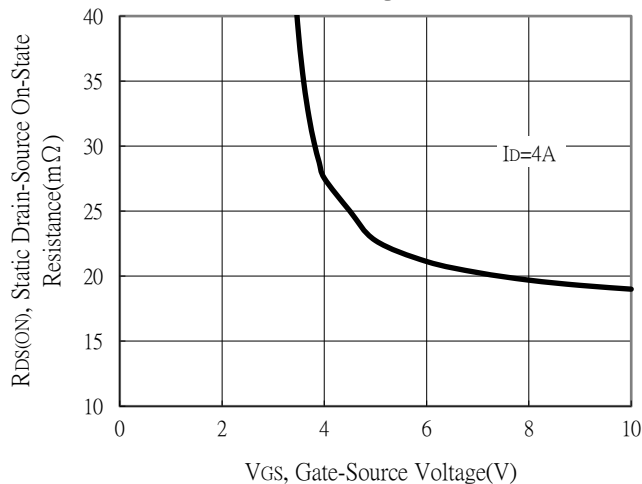
Static Drain-Source On-State resistance vs Drain Current



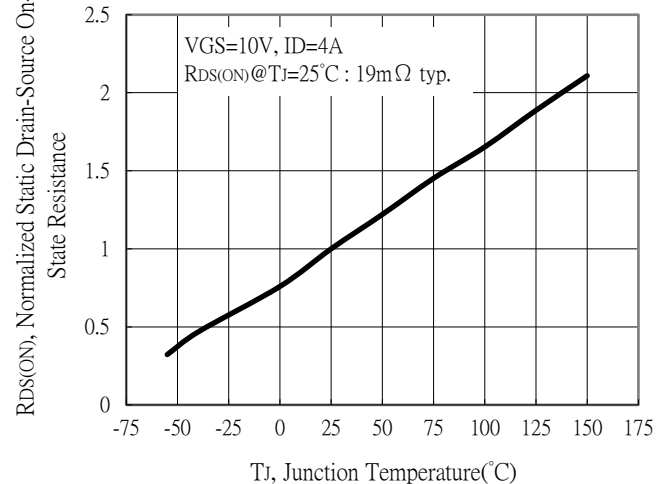
Body Diode Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

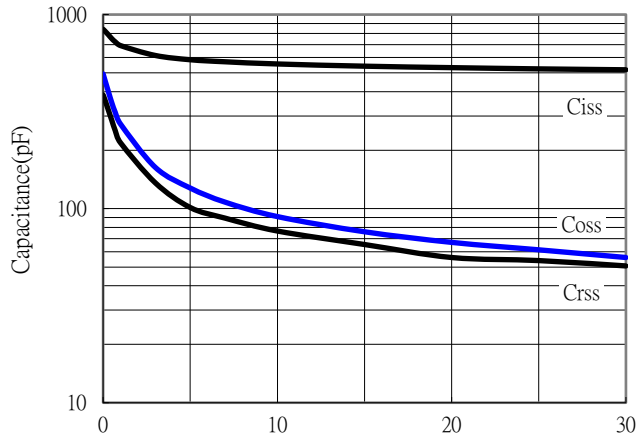


Drain-Source On-State Resistance vs Junction Temperature



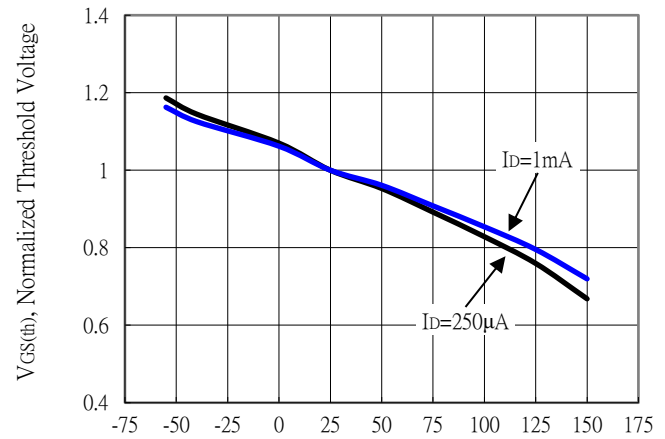
Typical Characteristics (Cont.) : Q1(N-channel)

Capacitance vs Drain-to-Source Voltage



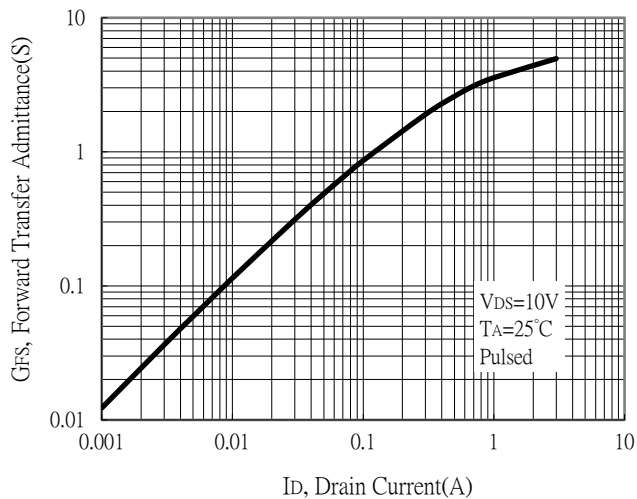
VDS, Drain-Source Voltage(V)

Threshold Voltage vs Junction Temperature



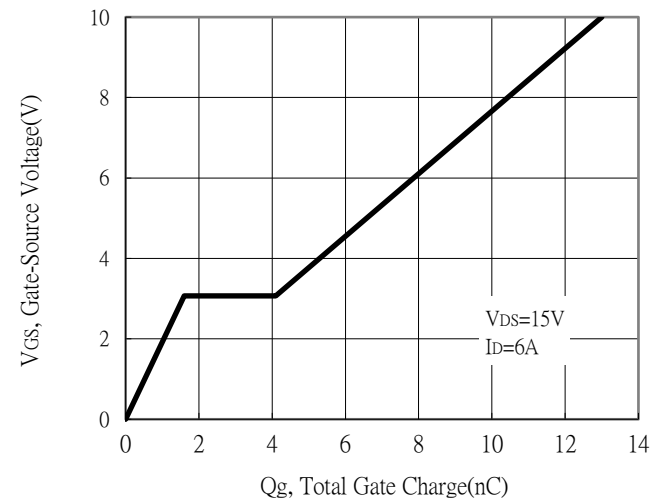
TJ, Junction Temperature(°C)

Forward Transfer Admittance vs Drain Current



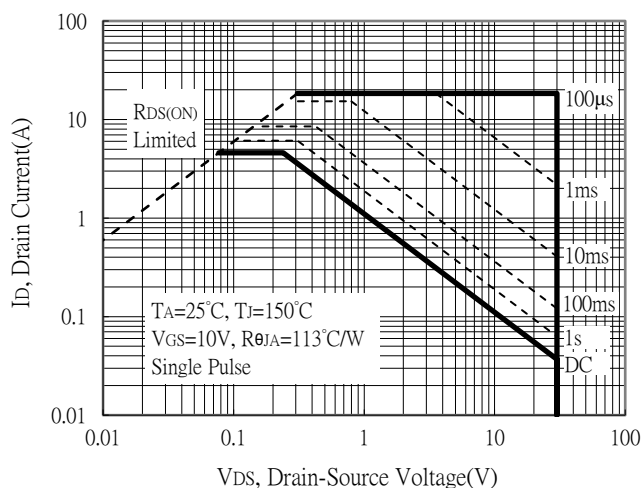
ID, Drain Current(A)

Gate Charge Characteristics



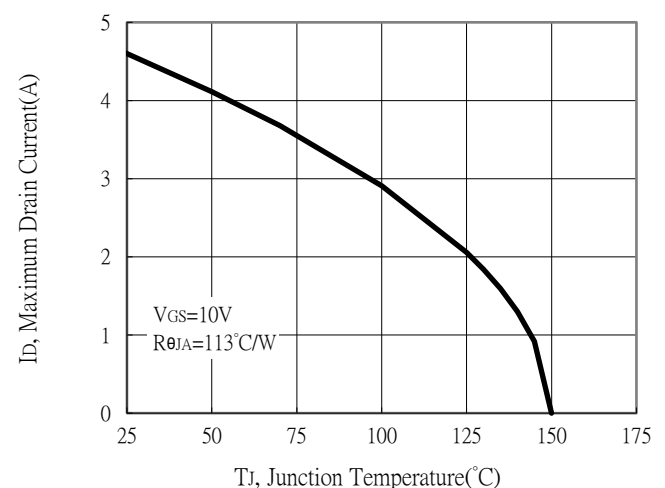
Qg, Total Gate Charge(nC)

Maximum Safe Operating Area



VDS, Drain-Source Voltage(V)

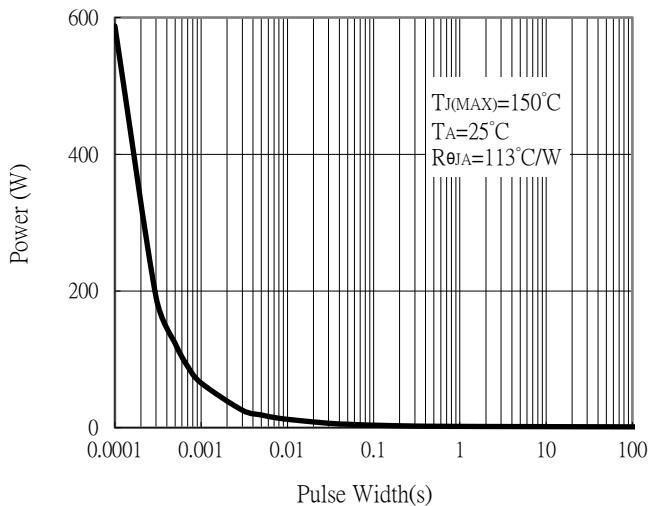
Maximum Drain Current vs Junction Temperature



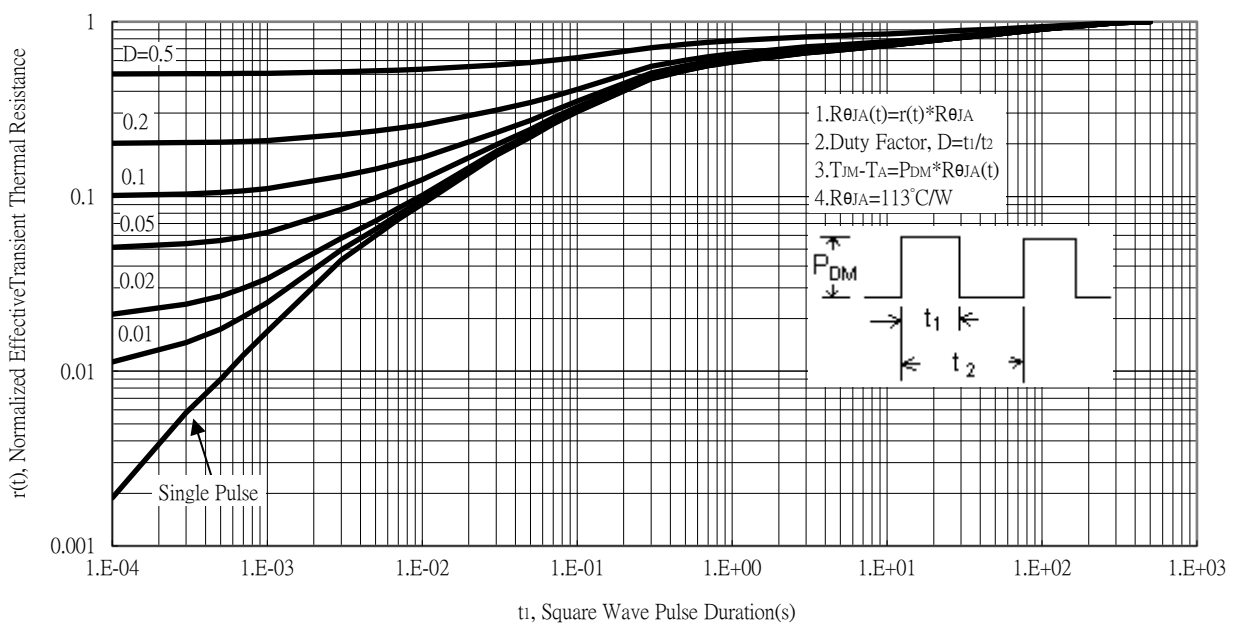
TJ, Junction Temperature(°C)

Typical Characteristics (Cont.) : Q1(N-channel)

Single Pulse Power Rating, Junction to Ambient

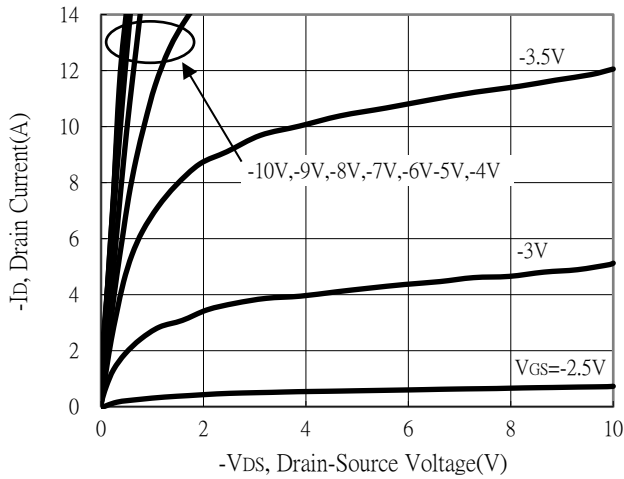


Transient Thermal Response Curves

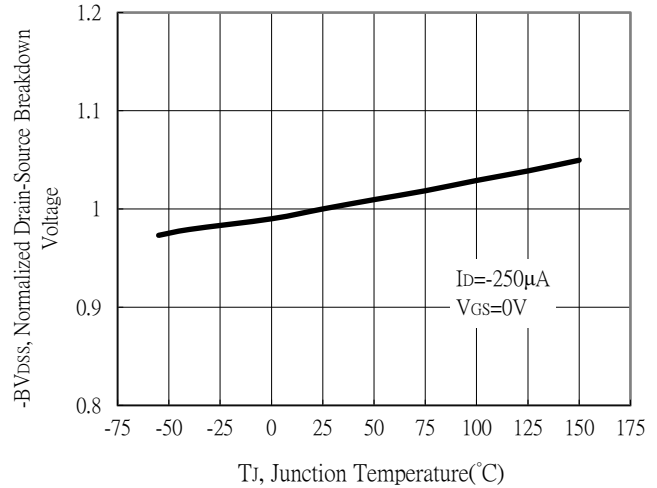


Typical Characteristics : Q2(P-channel)

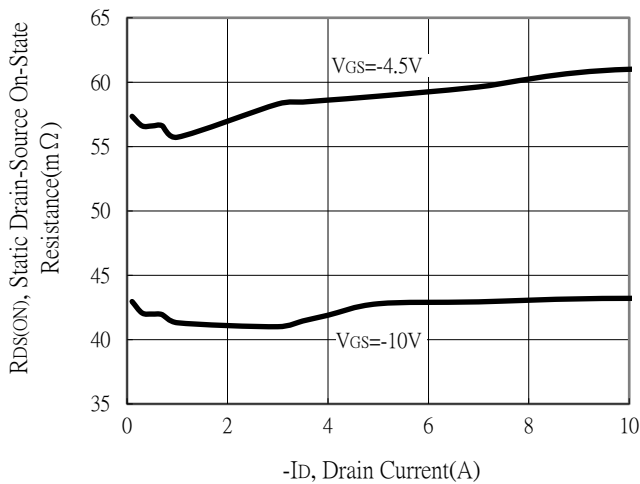
Typical Output Characteristics



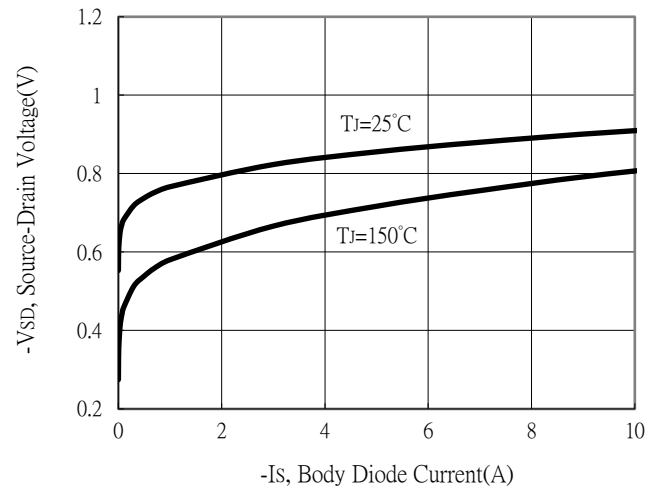
Breakdown Voltage vs Ambient Temperature



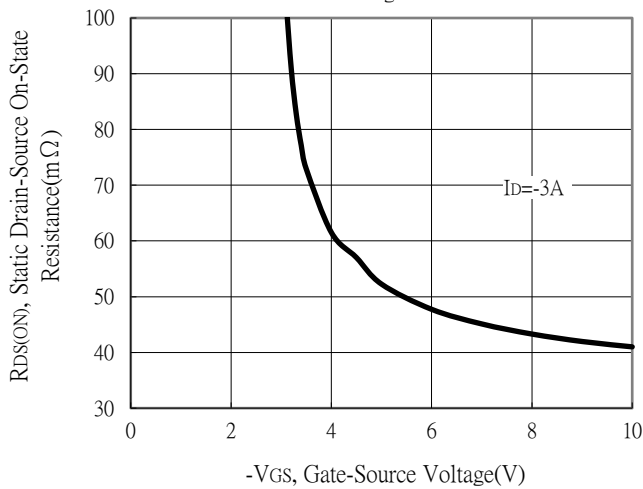
Static Drain-Source On-State resistance vs Drain Current



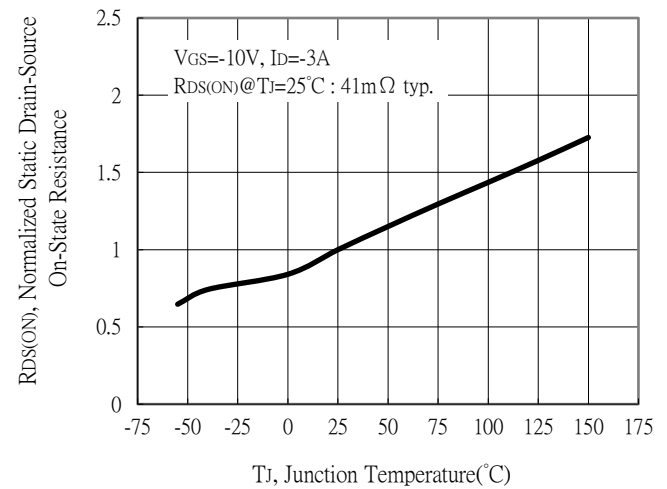
Body Diode Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

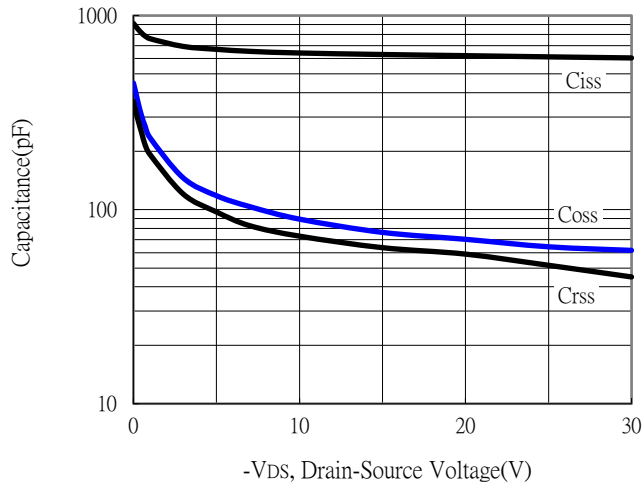


Drain-Source On-State Resistance vs Junction Temperature

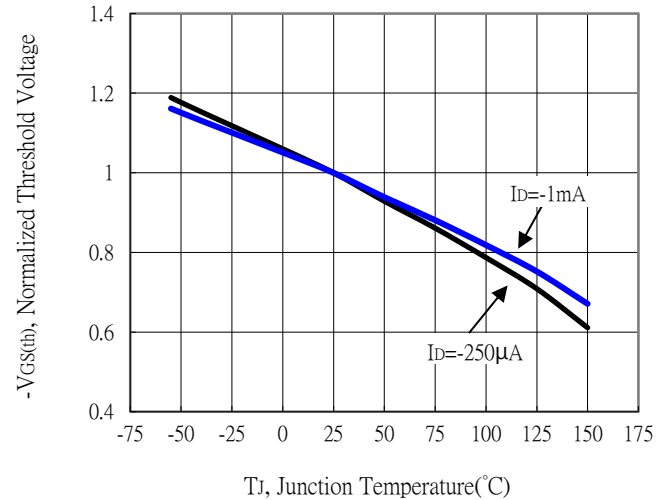


Typical Characteristics (Cont.) : Q2(P-channel)

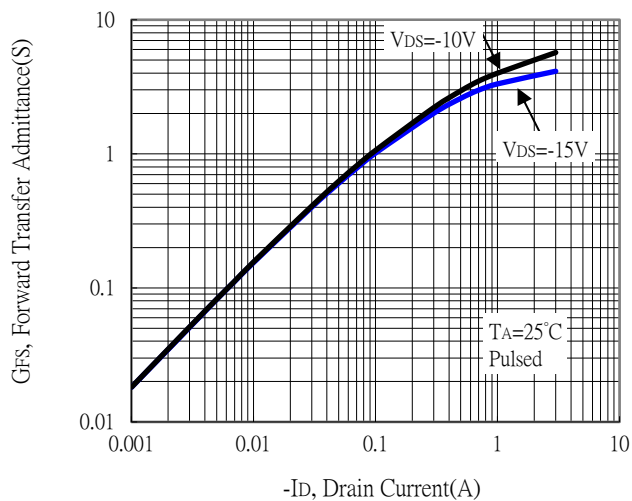
Capacitance vs Drain-to-Source Voltage



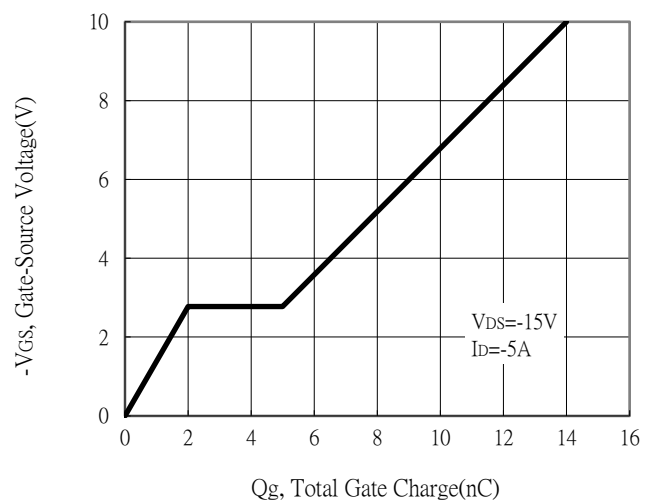
Threshold Voltage vs Junction Temperature



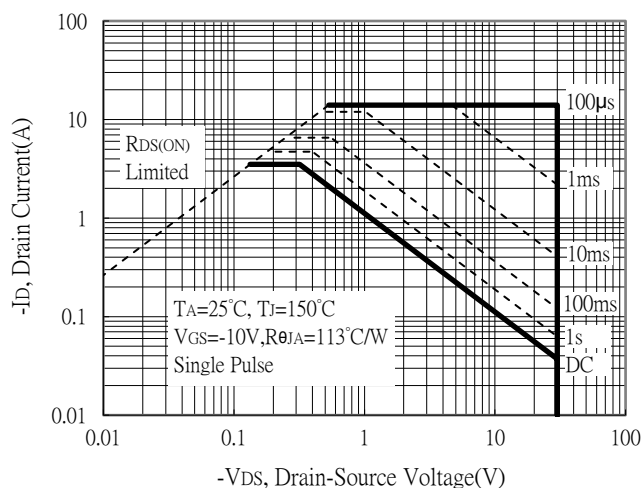
Forward Transfer Admittance vs Drain Current



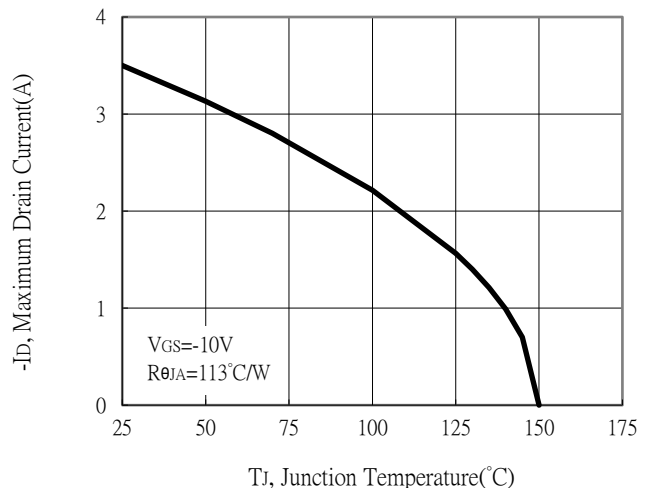
Gate Charge Characteristics



Maximum Safe Operating Area

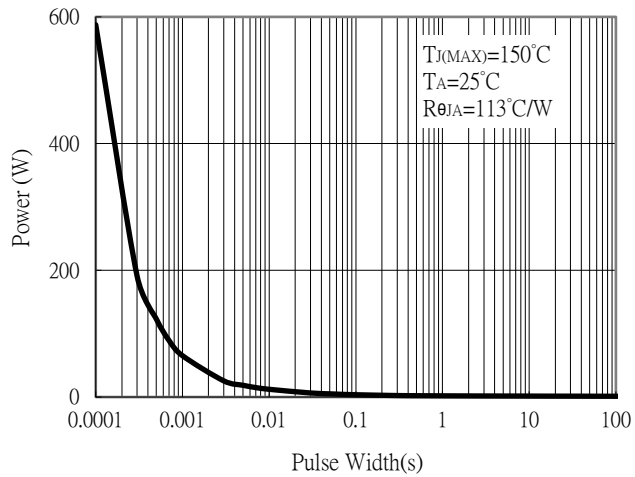


Maximum Drain Current vs Junction Temperature

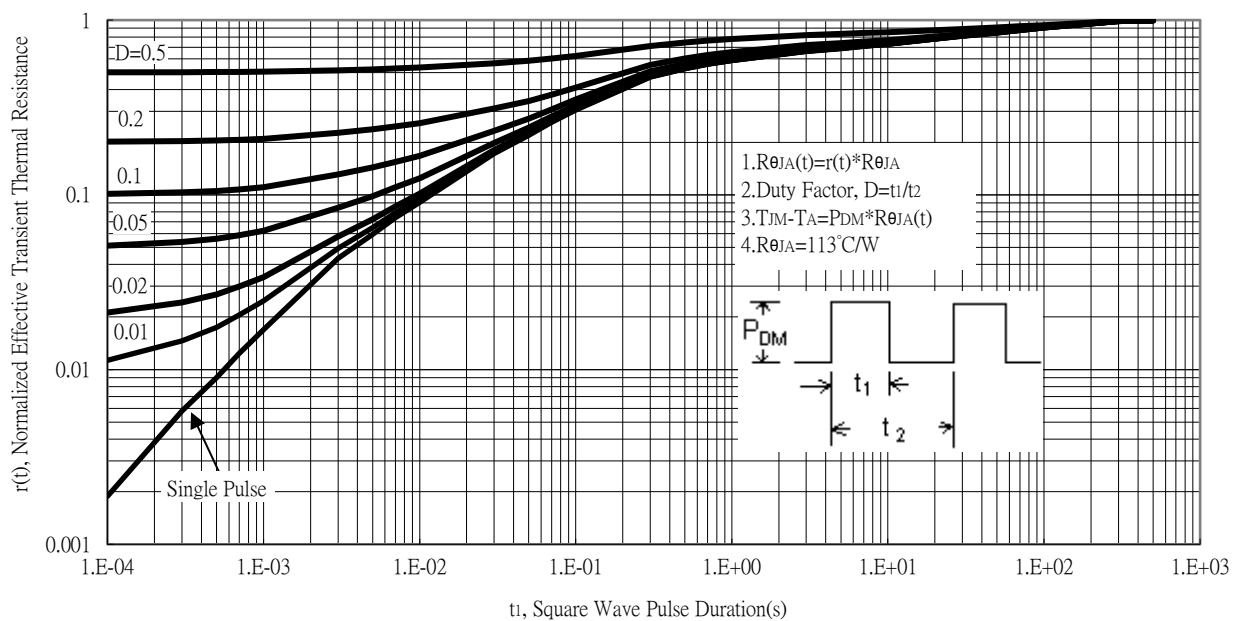


Typical Characteristics (Cont.) : Q2(P-channel)

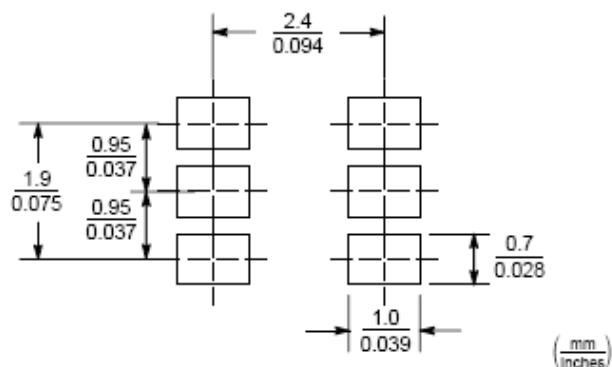
Single Pulse Power Rating, Junction to Ambient



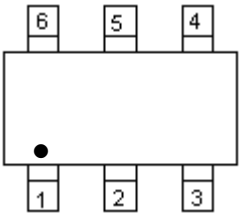
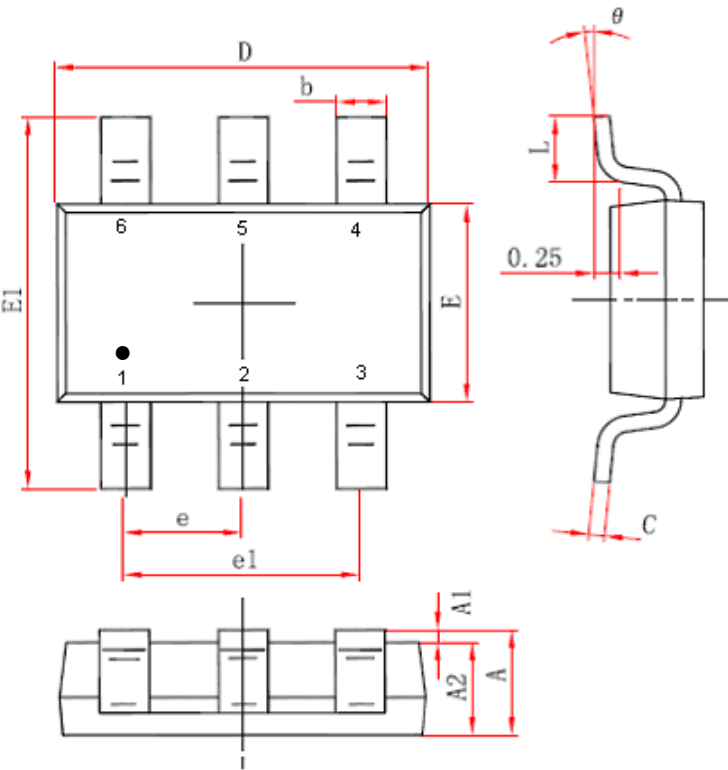
Transient Thermal Response Curves



Recommended Soldering Footprint



TSOP-6 Dimension



- Style:
Pin 1. Gate (G1)
Pin 2. Source (S2)
Pin 3. Gate (G2)
Pin 4. Drain (D2)
Pin 5. Source (S1)
Pin 6. Drain (D1)

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035	E	1.600	1.700	0.063	0.067
A1	0.000	0.100	0.000	0.004	E1	2.650	2.950	0.104	0.116
A2	0.700	0.800	0.028	0.031	e	0.95 BSC		0.037 BSC	
b	0.350	0.500	0.014	0.020	e1	1.90 BSC		0.075 BSC	
c	0.080	0.200	0.003	0.008	L	0.300	0.600	0.012	0.024
D	2.820	3.020	0.111	0.119	θ	0°	8°	0°	8°

Notes : 1.Controlling dimension : millimeters.